



AO8800

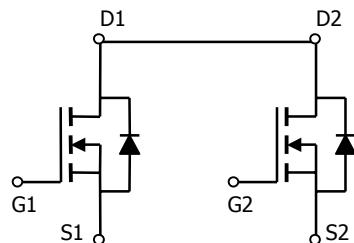
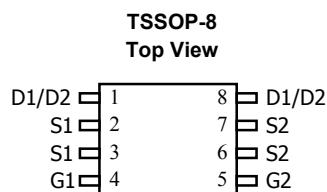
Common-Drain Dual N-Channel Enhancement Mode Field Effect Transistor

General Description

The AO8800 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V while retaining a 12V $V_{GS(MAX)}$ rating. This device is suitable for use as a uni-directional or bi-directional load switch, facilitated by its common-drain configuration.

Features

$V_{DS} (V) = 30V$
 $I_D = 6.4A$
 $R_{DS(ON)} < 24m\Omega (V_{GS} = 10V)$
 $R_{DS(ON)} < 30m\Omega (V_{GS} = 4.5V)$
 $R_{DS(ON)} < 40m\Omega (V_{GS} = 2.5V)$
 $R_{DS(ON)} < 70m\Omega (V_{GS} = 1.8V)$



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^A	I_D	6.4	A
$T_A=70^\circ C$		5.4	
Pulsed Drain Current ^B	I_{DM}	30	
Power Dissipation ^A	P_D	1.5	W
$T_A=70^\circ C$		1.08	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	64	83	°C/W
Maximum Junction-to-Ambient ^A		89	120	°C/W
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	53	70	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{\text{GS}}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=24\text{V}, V_{\text{GS}}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=\pm 12\text{V}$			100	nA
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_D=250\mu\text{A}$	0.6	0.8	1	V
$I_{\text{D}(\text{ON})}$	On state drain current	$V_{\text{GS}}=4.5\text{V}, V_{\text{DS}}=5\text{V}$	30			A
$R_{\text{DS}(\text{ON})}$	Static Drain-Source On-Resistance	$V_{\text{GS}}=10\text{V}, I_D=6.4\text{A}$ $T_J=125^\circ\text{C}$		20 28	24	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_D=6\text{A}$			30	$\text{m}\Omega$
		$V_{\text{GS}}=2.5\text{V}, I_D=5\text{A}$			40	$\text{m}\Omega$
		$V_{\text{GS}}=1.8\text{V}, I_D=2.5\text{A}$			70	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{\text{DS}}=5\text{V}, I_D=5\text{A}$	10	17		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}, V_{\text{GS}}=0\text{V}$			0.66	V
I_S	Maximum Body-Diode Continuous Current				2.4	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=15\text{V}, f=1\text{MHz}$		767		pF
C_{oss}	Output Capacitance			111		pF
C_{rss}	Reverse Transfer Capacitance			82		pF
R_g	Gate resistance	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=0\text{V}, f=1\text{MHz}$		1.3		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{\text{GS}}=4.5\text{V}, V_{\text{DS}}=15\text{V}, I_D=6.4\text{A}$		10		nC
Q_{gs}	Gate Source Charge			1.2		nC
Q_{gd}	Gate Drain Charge			3.1		nC
$t_{\text{D}(\text{on})}$	Turn-On Delay Time	$V_{\text{GS}}=10\text{V}, V_{\text{DS}}=15\text{V}, R_L=2.4\Omega, R_{\text{GEN}}=6\Omega$		5		ns
t_r	Turn-On Rise Time			5.5		ns
$t_{\text{D}(\text{off})}$	Turn-Off Delay Time			39		ns
t_f	Turn-Off Fall Time			4.7		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=5\text{A}, \text{d}I/\text{d}t=100\text{A}/\mu\text{s}$		15		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=5\text{A}, \text{d}I/\text{d}t=100\text{A}/\mu\text{s}$		7.1		nC

A: The value of R_{0JA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

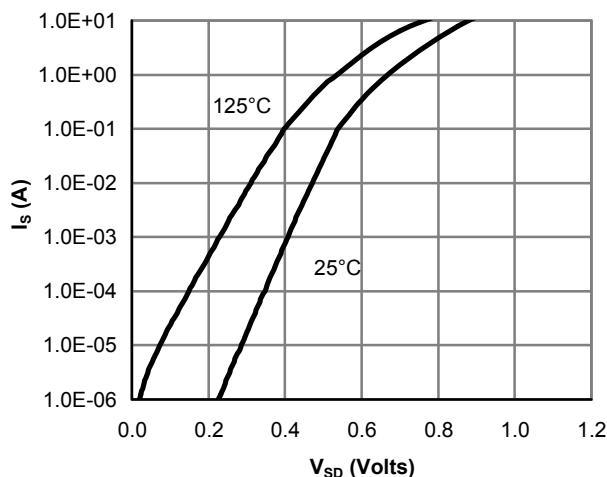
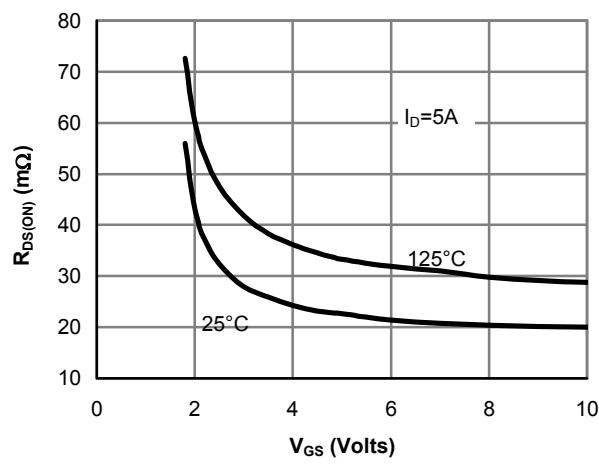
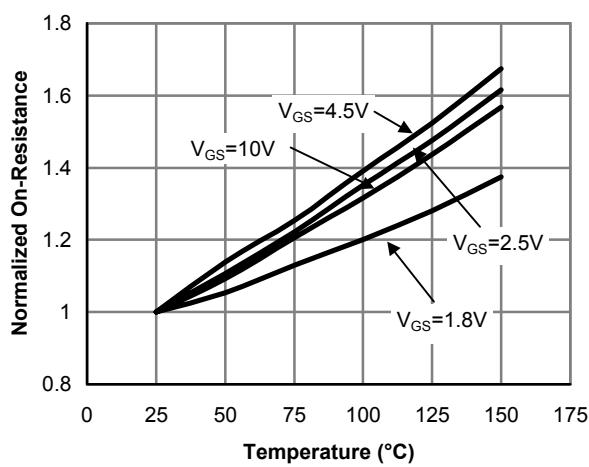
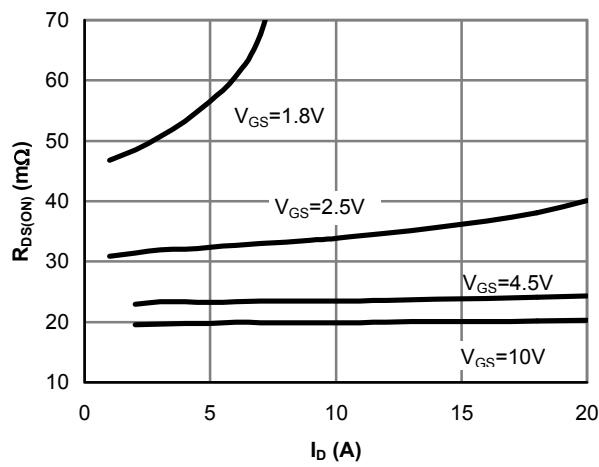
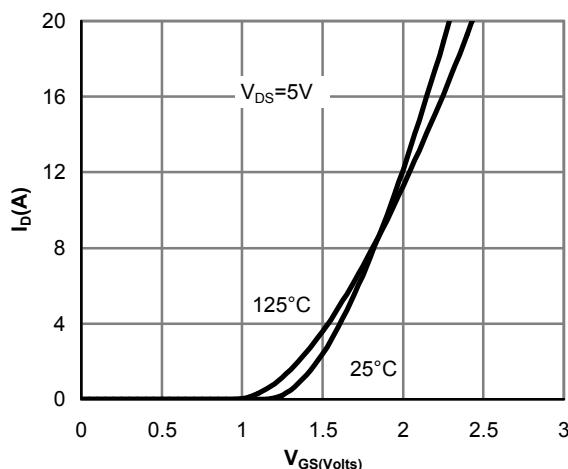
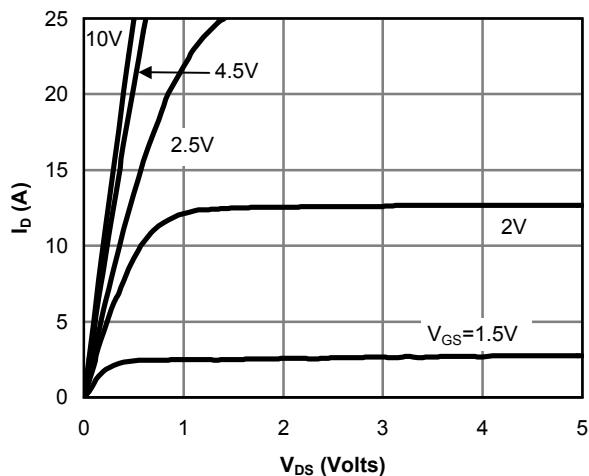
B: Repetitive rating, pulse width limited by junction temperature.

C. The R_{0JA} is the sum of the thermal impedance from junction to lead R_{0JL} and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



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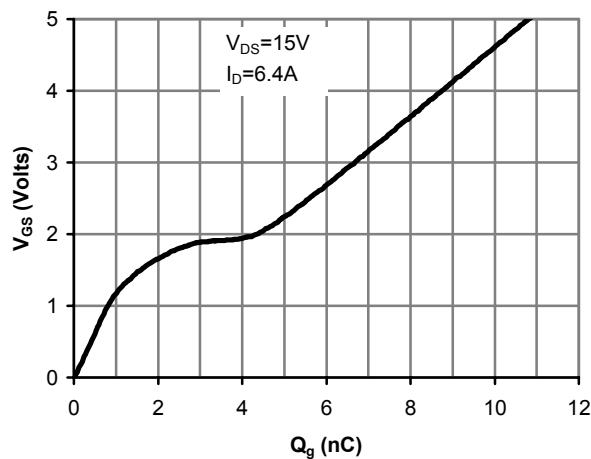


Figure 7: Gate-Charge Characteristics

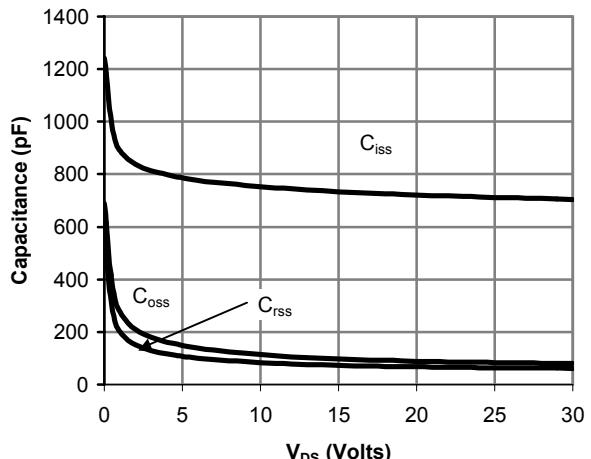


Figure 8: Capacitance Characteristics

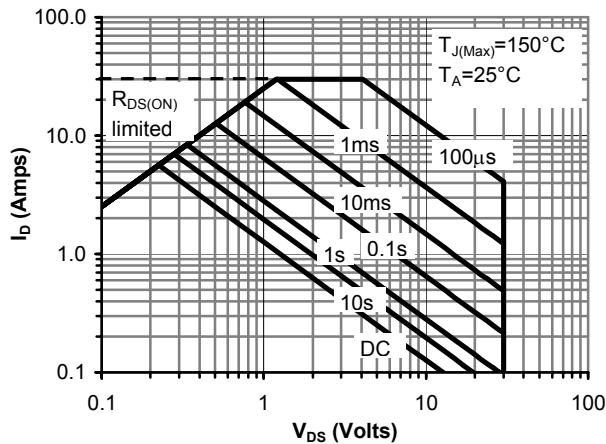


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

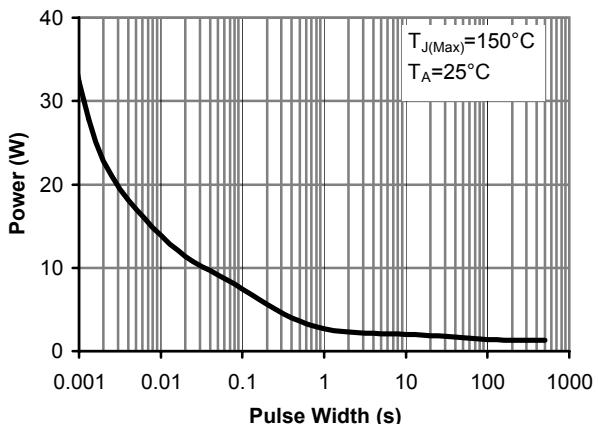


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

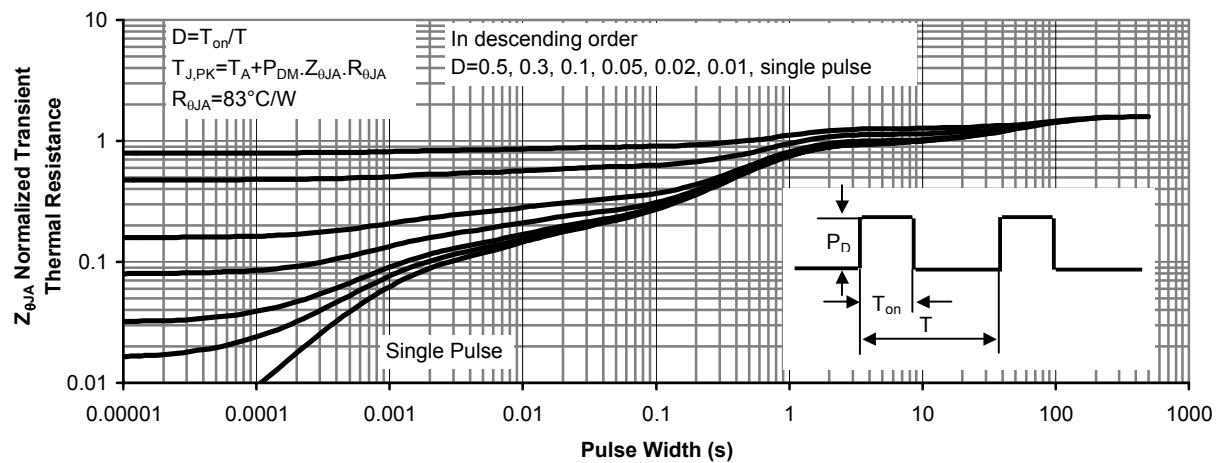
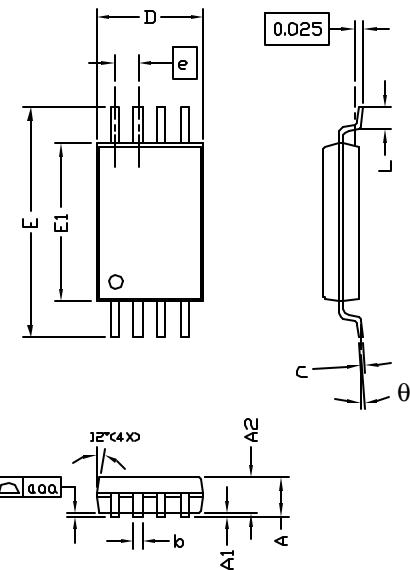


Figure 11: Normalized Maximum Transient Thermal Impedance



ALPHA & OMEGA
SEMICONDUCTOR, INC.

TSSOP-8 Package Data



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	—	—	1.20	—	—	0.047
A1	0.05	—	0.15	0.002	—	0.006
A2	0.80	1.00	1.05	0.031	0.039	0.041
b	0.19	—	0.30	0.007	—	0.012
c	0.09	—	0.20	0.004	—	0.008
D	2.90	3.00	3.10	0.114	0.118	0.122
E	6.40 BSC			0.252 BSC		
E1	4.30	4.40	4.50	0.169	0.173	0.177
e	0.65 BSC			0.0259 (REF)		
L	0.45	0.60	0.75	0.018	0.024	0.030
y	—	—	0.10	—	—	0.004
θ	0°	—	8°	0°	—	8°

NOTE:

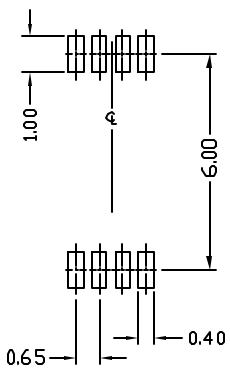
1. LEAD FINISH: 150 MICROINCHES (3.8 μ m) MIN.
THICKNESS OF Tin/Lead (SOLDER) PLATED ON LEAD
2. TOLERANCE ± 0.100 mm (4 mil) UNLESS OTHERWISE
SPECIFIED
3. COPLANARITY : 0.1000 mm
4. DIMENSION L IS MEASURED IN GAGE PLANE

PACKAGE MARKING DESCRIPTION



NOTE:
 LG - AOS LOGO
 PARTN - PART NUMBER CODE.
 F - FAB LOCATION
 A - ASSEMBLY LOCATION
 W - WEEK CODE.
 LN - ASSEMBLY LOT CODE

RECOMMENDED LAND PATTERN



TSSOP-8 PART NO. CODE

PART NO.	CODE	PART NO.	CODE	PART NO.	CODE
AO8800	8800				
AO8701	8701				

UNIT: mm

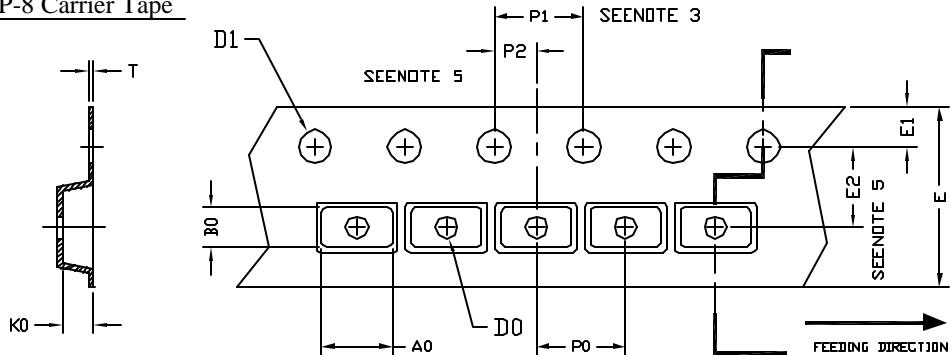


ALPHA & OMEGA

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TSSOP-8 Tape and Reel Data

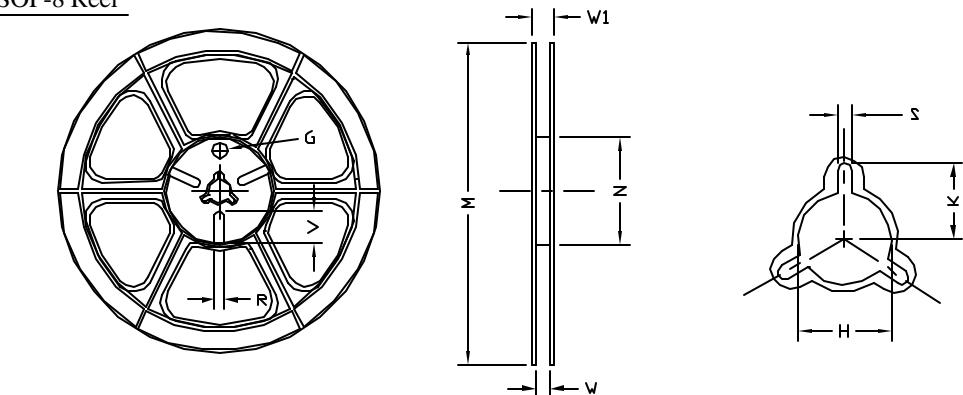
TSSOP-8 Carrier Tape



UNIT MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SQ-8 (12 mm)	6.80 ± 0.10	3.40 ± 0.10	1.60 ± 0.10	150 ± 0.10	1.30 MIN.	12.00 ± 0.30	1.75 ± 0.10	5.50 ± 0.05	8.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	0.30 ± 0.05

TSSOP-8 Reel



UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	Ø330	Ø178.00 ±0.50	Ø60.00 ±0.50	13.00 +1.50 -0.00	16.00 ±1.00	Ø13.50 ±0.50	10.60	2.20 ±0.50	---	---	---

TSSOP-8 Tape

Leader / Trailer & Orientation

